Type	L #	Hits	Search Text	DBs	Time Stamp	Com ment s	or Defi nitio n	Err ro rs
BRS	L1	15	(oxide$1 or dioxide$1) with (BOE or (buffer adj oxide adj etch$4) or DHF or (dilut$4 adj HF)) with (SC1 or "SC1" or SC-1 or "SC-1") with etch$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 15:37			0

03/04/2004, EAST Version: 1.4.1

Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
BRS	L1	26173	floating adj gate$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 11:08			0
BRS	L2	46375	control$4 adj gate$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 11:08			0
BRS	L3	89839	STI$1 or "STI" or (shallow adj trench$2 adj isolat$4) or shallow-trench-isolation $1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 11:08			0
BRS	L4	1095	1 and 2 and 3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 11:09			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Definitions	Errors
5	BRS	L5	1451	(recess$4 or etch$4 or clean$4 or pre-treat$4 or pretreat$4 or treat$5) near10 (tunnel$4 near3 (oxide$1 or dielectric or insulat$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 12:00			0
6	BRS	L6	225	4 and 5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 11:38			0
7	IS&R	L7	1	("20030124800").PN.	USPAT; US-PGPUB	2004/03/04 11:39			0
8	IS&R	L8	2	(("20030119256") or ("20020167041")).PN.	USPAT; US-PGPUB	2004/03/04 11:40			0
9	BRS	L9	69	(recess$4) near10 (tunnel$4 near3 (oxide$1 or dielectric or insulat$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 12:00			0

L Number	Hits	Search Text	DB	Time stamp
1	26173	floating adj gate$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 11:08
2	46375	control$4 adj gate$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 11:08
3	89839	STI$1 or "STI" or (shallow adj trench$2 adj isolat$4) or shallow-trench-isolation$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 11:08
4	1095	(floating adj gate$1) and (control$4 adj gate$1) and (STI$1 or "STI" or (shallow adj trench$2 adj isolat$4) or shallow-trench-isolation$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 11:09
5	1451	(recess$4 or etch$4 or clean$4 or pre-treat$4 or pretreat$4 or treat$5) near10 (tunnel$4 near3 (oxide$1 or dielectric or insulat$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 12:00
6	225	((floating adj gate$1) and (control$4 adj gate$1) and (STI$1 or "STI" or (shallow adj trench$2 adj isolat$4) or shallow-trench-isolation$1)) and ((recess$4 or etch$4 or clean$4 or pre-treat$4 or pretreat$4 or treat$5) near10 (tunnel$4 near3 (oxide$1 or dielectric or insulat$4)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 11:38
7	1	("20030124800").PN.	USPAT; US-PGPUB	2004/03/04 11:39
8	2	(("20030119256") or ("20020167041")).PN.	USPAT; US-PGPUB	2004/03/04 11:40
9	69	(recess$4) near10 (tunnel$4 near3 (oxide$1 or dielectric or insulat$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 12:00
-	23068	floating adj gate$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 11:08
-	42151	control$4 adj gate$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 11:08
-	14645	(floating adj gate$1) and (control$4 adj gate$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/25 13:29
-	77326	STI$1 or "STI" or (shallow adj trench$2 adj isolat$4) or shallow-trench-isolation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/04 11:08

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-	717	((floating adj gate$1) and (control$4 adj gate$1)) and (STI$1 or "STI" or (shallow adj trench$2 adj isolat$4) or shallow-trench-isolation)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/25 13:32
-	33600	CMP or "CMP" or chemical-mechanical-polishing or (chemical adj mechanical adj polish$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/10 12:37
-	381	(((floating adj gate$1) and (control$4 adj gate$1)) and (STI$1 or "STI" or (shallow adj trench$2 adj isolat$4) or shallow-trench-isolation)) and (CMP or "CMP" or chemical-mechanical-polishing or (chemical adj mechanical adj polish$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/25 13:33
-	24241	floating adj (gate or gates)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/10 12:35
-	32533	control adj (gate or gates)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/10 12:36
-	81667	STI$1 or "STI" or (shallow adj trench$2 adj isolat$4) or shallow-trench-isolation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/10 12:36
-	37103	CMP or "CMP" or chemical-mechanical-polishing or (chemical adj mechanical adj polish$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/10 12:37
-	15204	(floating adj (gate or gates)) and (control adj (gate or gates))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/10 12:38
-	455	(floating adj (gate or gates)) and (control adj (gate or gates)) and (STI$1 or "STI" or (shallow adj trench$2 adj isolat$4) or shallow-trench-isolation) and (CMP or "CMP" or chemical-mechanical-polishing or (chemical adj mechanical adj polish$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/10 12:38
-	24266	protru$8 with (trench$2 or dielectric$1 or insulat$5 or oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/10 12:40
-	67	((floating adj (gate or gates)) and (control adj (gate or gates)) and (STI$1 or "STI" or (shallow adj trench$2 adj isolat$4) or shallow-trench-isolation) and (CMP or "CMP" or chemical-mechanical-polishing or (chemical adj mechanical adj polish$4))) and (protru$8 with (trench$2 or dielectric$1 or insulat$5 or oxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/10 12:59
-	22	trench$2 with (corner$1 or edge$1) with round$4 with (hydrogen or H2 or "H2" or "H.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/10 13:04

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-	84	trench$2 with (hydrogen or H2 or "H2" or "H.sub.2") with anneal$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/10 13:07
-	1	(trench$2 with (hydrogen or H2 or "H2" or "H.sub.2") with anneal$4) and (((floating adj (gate or gates)) and (control adj (gate or gates)) and (STI$1 or "STI" or (shallow adj trench$2 adj isolat$4) or shallow-trench-isolation) and (CMP or "CMP" or chemical-mechanical-polishing or (chemical adj mechanical adj polish$4))) and (protru$8 with (trench$2 or dielectric$1 or insulat$5 or oxide)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/10 13:05
-	2195	(wet near4 (oxidi$8 or oxida$8)) with oxide$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/10 13:08
-	17	(N2 or "N2" or "N.sub.2") with ((wet near4 (oxidi$8 or oxida$8)) with oxide$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/10 13:09
-	91	(poly$1 or polysilicon or (polycrystal$8 adj silicon)) with (LPCVD or LP-CVD or (low adj pressure adj chemical adj vapor adj deposit$5) or ((LP or (low adj pressure)) adj (CVD or (chemical adj vapor adj deposit$5)))) with (silane or disilane or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6") with (Ph3 or "Ph3" or "Ph.sub.3" or "P H.sub.3")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/10 14:42
-	3149	((silicon adj nitride) or Si3N4 or "Si3N4" or "Si.sub.3N.sub.4" or "Si.sub.3 N.sub.4") with (H3PO4 or "H3PO4" or "H.sub.3PO.sub.4" or "H.sub.3 P O.sub.4" or "H.sub.3 PO.sub.4" or "H.sub.3P O.sub.4" or (phosphoric adj acid$1) or phosphoricacid$1 or phosphoric-acid$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/10 14:43
-	201	(poly$1 or polysilicon or (polycrystal$8 adj silicon)) with (LPCVD or LP-CVD or (low adj pressure adj chemical adj vapor adj deposit$5) or ((LP or (low adj pressure)) adj (CVD or (chemical adj vapor adj deposit$5)))) with (silane$1 or disilane$1 or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6") with (Ph3 or "Ph3" or "Ph.sub.3" or "P H.sub.3" or phosphine$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/10 14:44
-	47	(((silicon adj nitride) or Si3N4 or "Si3N4" or "Si.sub.3N.sub.4" or "Si.sub.3 N.sub.4") with (H3PO4 or "H3PO4" or "H.sub.3PO.sub.4" or "H.sub.3 P O.sub.4" or "H.sub.3 PO.sub.4" or "H.sub.3P O.sub.4" or (phosphoric adj acid$1) or phosphoricacid$1 or phosphoric-acid$1)) and ((poly$1 or polysilicon or (polycrystal$8 adj silicon)) with (LPCVD or LP-CVD or (low adj pressure adj chemical adj vapor adj deposit$5) or ((LP or (low adj pressure)) adj (CVD or (chemical adj vapor adj deposit$5)))) with (silane$1 or disilane$1 or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6") with (Ph3 or "Ph3" or "Ph.sub.3" or "P H.sub.3" or phosphine$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/10 14:45
-	0	((((silicon adj nitride) or Si3N4 or "Si3N4" or "Si.sub.3N.sub.4" or "Si.sub.3 N.sub.4") with (H3PO4 or "H3PO4" or "H.sub.3PO.sub.4" or "H.sub.3 P O.sub.4" or "H.sub.3 PO.sub.4" or "H.sub.3P O.sub.4" or (phosphoric adj acid$1) or phosphoricacid$1 or phosphoric-acid$1)) and ((poly$1 or polysilicon or (polycrystal$8 adj silicon)) with (LPCVD or LP-CVD or (low adj pressure adj chemical adj vapor adj deposit$5) or ((LP or (low adj pressure)) adj (CVD or (chemical adj vapor adj deposit$5)))) with (silane$1 or disilane$1 or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6") with (Ph3 or "Ph3" or "Ph.sub.3" or "P H.sub.3" or phosphine$1))) and (trench$2 with (hydrogen or H2 or "H2" or "H.sub.2") with anneal$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/10 14:45

| - | | 2 | (((((silicon adj nitride) or Si3N4 or "Si3N4" or "Si.sub.3N.sub.4" or "Si.sub.3 N.sub.4") with (H3PO4 or "H3PO4" or "H.sub.3PO.sub.4" or "H.sub.3 P O.sub.4" or "H.sub.3 PO.sub.4" or "H.sub.3P O.sub.4" or (phosphoric adj acid$1) or phosphoricacid$1 or phosphoric-acid$1)) and ((poly$1 or polysilicon or (polycrystal$8 adj silicon)) with (LPCVD or LP-CVD or (low adj pressure adj chemical adj vapor adj deposit$5) or ((LP or (low adj pressure)) adj (CVD or (chemical adj vapor adj deposit$5)))) with (silane$1 or disilane$1 or SiH4 or "SiH4" or "SiH.sub.4" or "Si H.sub.4" or Si2H6 or "Si2H6" or "Si.sub.2H.sub.6" or "Si.sub.2 H.sub.6") with (Ph3 or "Ph3" or "Ph.sub.3" or "P H.sub.3" or phosphine$1))) and (floating adj (gate or gates)) and (control adj (gate or gates)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/08/10 14:45 |